

ABSTRACT OF THE DISCLOSURE

For crystallizing an amorphous semiconductor film by means of irradiation of laser beams, a top surface and a back surface of the amorphous semiconductor film are irradiated with the laser beams. In this case, an effective energy intensity  $I_0$  of the laser beams to be applied onto the top surface and an effective energy intensity  $I_0'$  of the laser beams to be applied onto the back surface satisfy the relationship of  $0 < I_0'/I_0 < 1$  or  $1 < I_0'/I_0$ . Thus, a laser annealing method capable of providing a crystalline semiconductor film with large grain diameters can be provided.

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